

N-channel TrenchMOS standard level FET 19 May 2016

Product data sheet

General description 1.

Standard level N-channel MOSFET in a SOT226 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

Features and benefits 2.

- AEC Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with $V_{GS(th)}$ rating of greater than 1 V at 175 °C •

3. Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications •
- Transmission control
- Ultra high performance power switching •

4. Quick reference data

Table 1. Qui	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	324	W
Static charact	teristics			1			
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11		-	1.5	1.9	mΩ
Dynamic char	acteristics			1			
Q _{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V; Fig. 13; Fig. 14		-	34.7	-	nC

[1] Continuous current is limited by package.

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G C C
mb	D	mounting base; connected to drain	I 2 3 I 2PAK (SOT226)	mbb076 S

6. Ordering information

Table 3. Ordering information						
Type number Package						
	Name	Description	Version			
BUK7E1R9-40E	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7E1R9-40E	BUK7E1R9-40E

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	40	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	324	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	120	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	1198	А
T _{stg}	storage temperature			-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	1198	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} & I_{D} = 120 \; A; V_{sup} \leq 40 \; V; R_{GS} = 50 \; \Omega; \\ & V_{GS} = 10 \; V; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped; \\ & \overline{Fig. 4} \end{split}$	[2][3]	-	801	mJ

[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.

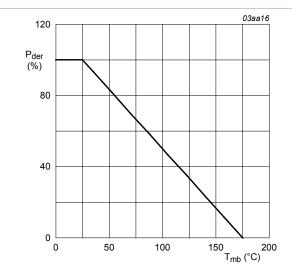
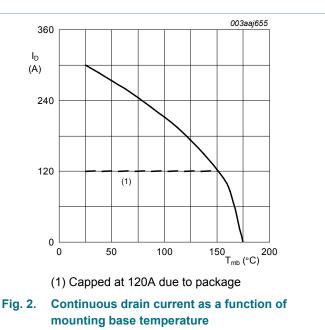


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

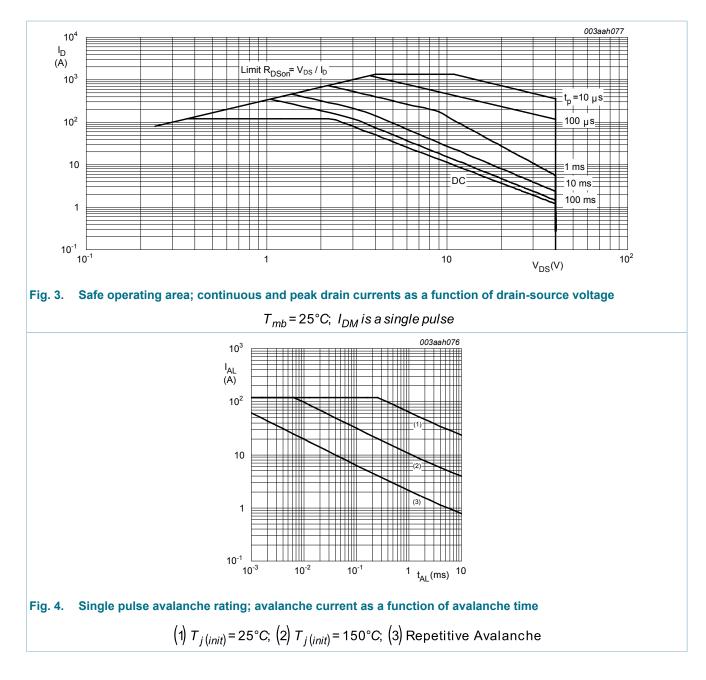
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



 $V_{GS} \ge 10V$

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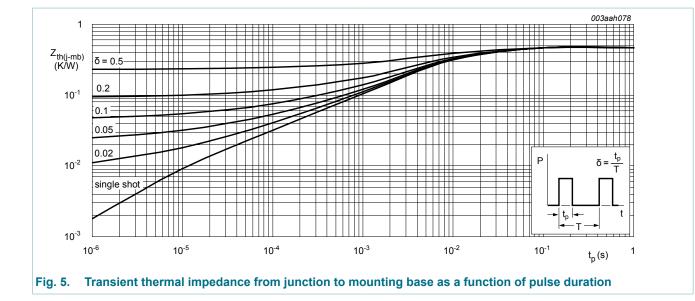
9. Thermal characteristics

Ible 6. I hermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	0.46	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air		-	65	-	K/W

Table 6. Thermal characteristics

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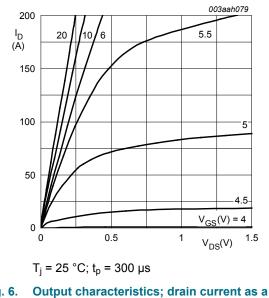


10. Characteristics

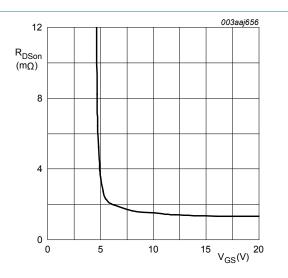
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·				_,
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
V _{GS(th)} gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9;</u> Fig. 10	2.4	3	4	V	
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; Fig. 10	-	-	4.5	V
	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; Fig. 10	1	-	-	V	
I _{DSS} drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.27	3	μA	
	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA	
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	1.5	1.9	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	3.6	mΩ
Dynamic cl	naracteristics	· · ·				
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V;	-	118	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	29.3	-	nC
Q _{GD}	gate-drain charge		-	34.7	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	7873	10472	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	1410	1692	pF
C _{rss}	reverse transfer capacitance	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V; R _{G(ext)} = 5 Ω	-	851	1165	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V;	-	35	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	49	-	ns
t _{d(off)}	turn-off delay time		-	87	-	ns
t _f	fall time		-	52	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L _S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	iin diode			1	1	,
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.79	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V;	-	46	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	62	-	nC





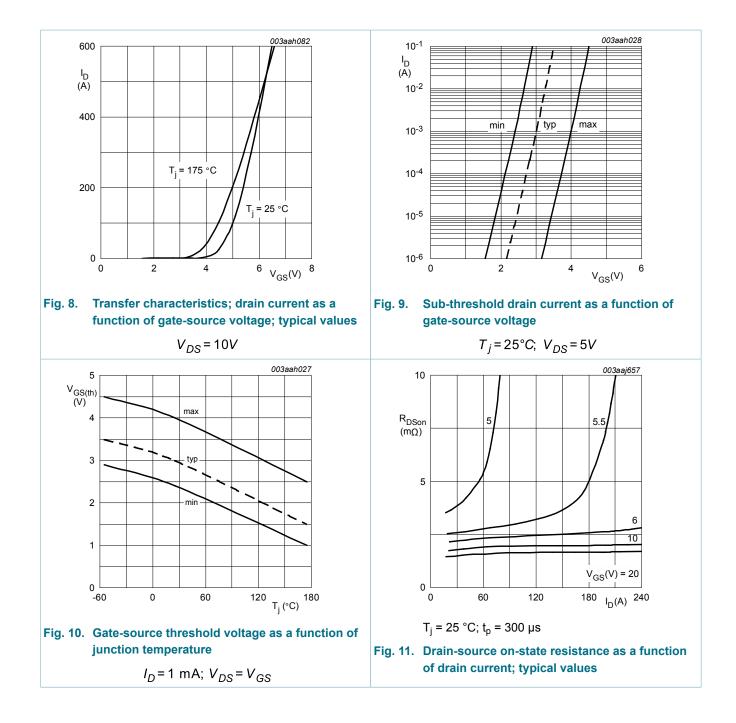




 $T_j = 25^{\circ}C; I_D = 25A$

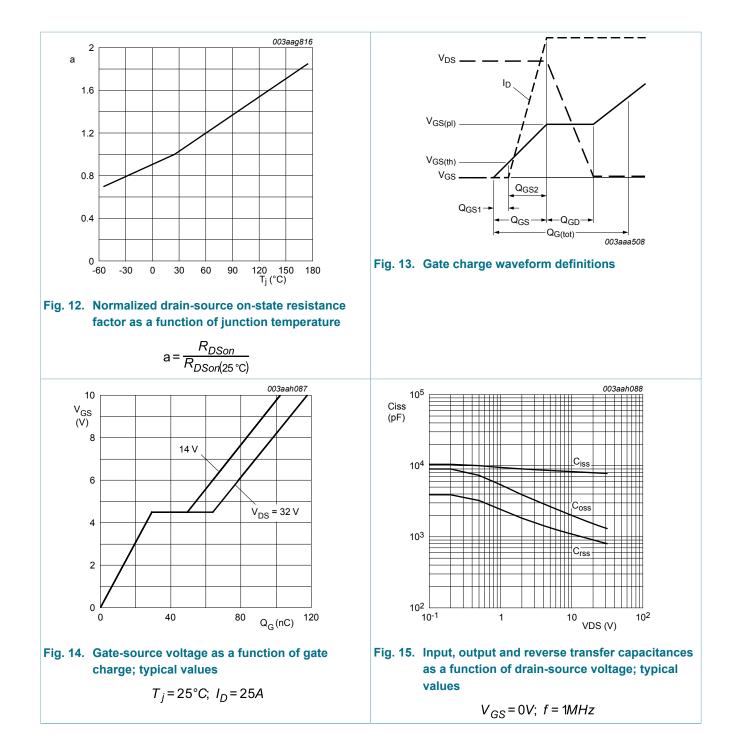
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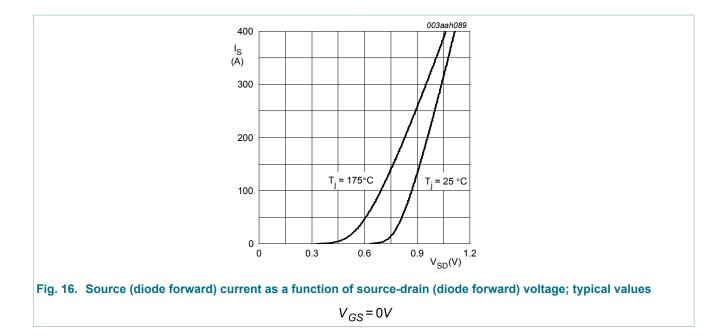
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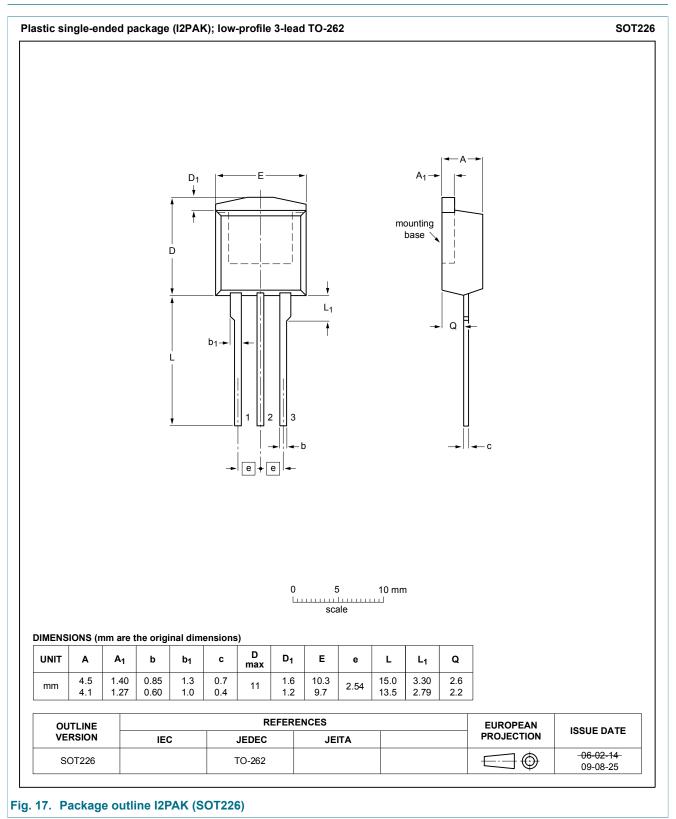
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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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